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# *Optimization of the Baking Process for ILC Project*

*Bernard VISENTIN*

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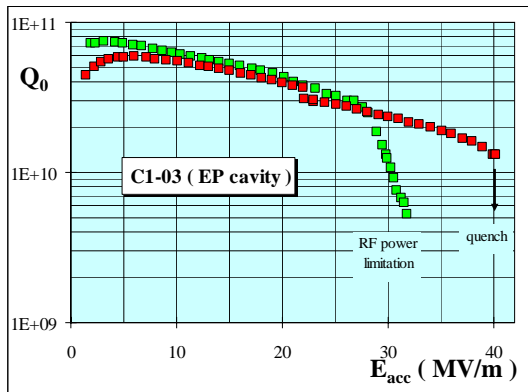


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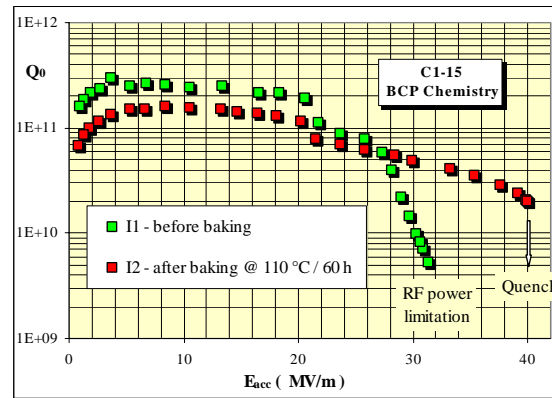
# Baking $\equiv$ Recipe for high gradients

$T = 110 - 120 \text{ }^\circ\text{C}$       $t = 1 - 2 \text{ days}$

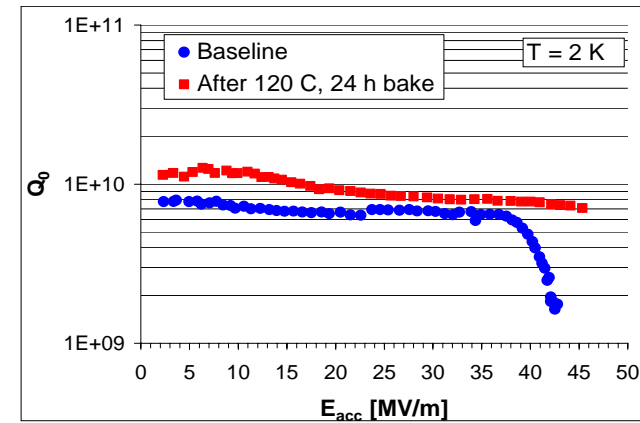
(Narrow Tuning Range)



1.3 GHz - Saclay / KEK  
Electropolishing  
Poly-crystal



1.3 GHz - Saclay  
Chemical etching  
Poly-crystal



2.2 GHz - JLab  
Chemical etching  
Single crystal

Whatever the niobium structure... (Single or Poly-crystal,)

Whatever the fabrication method...(EB Welding or Hydroforming, bulk Nb or clad Nb/Cu)

Whatever the chemical treatment... (Electropolishing or Buffered Chemical Polishing)

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# Standard Preparation

Heat Treatment 800°C ( H ) / 1300°C+Ti ( O-K<sub>T</sub> )

Ultrasonic Grease Remover

Chemical Etching (BCP) - FNP (1:1:2)  
Electropolishing (EP)

Ultra pure Water Rinse

{

High Pressure Rinse - 85 bars (FE)

Air-Drying : RT - 3 hours

Assembly + Helium Test

{

( RF Test )

« in-situ » Baking : 110 °C - 2 days

RF Test

Clean Room  
( Class 100 )

Test Stand  
( Vertical Cryostat )



30/4/2002

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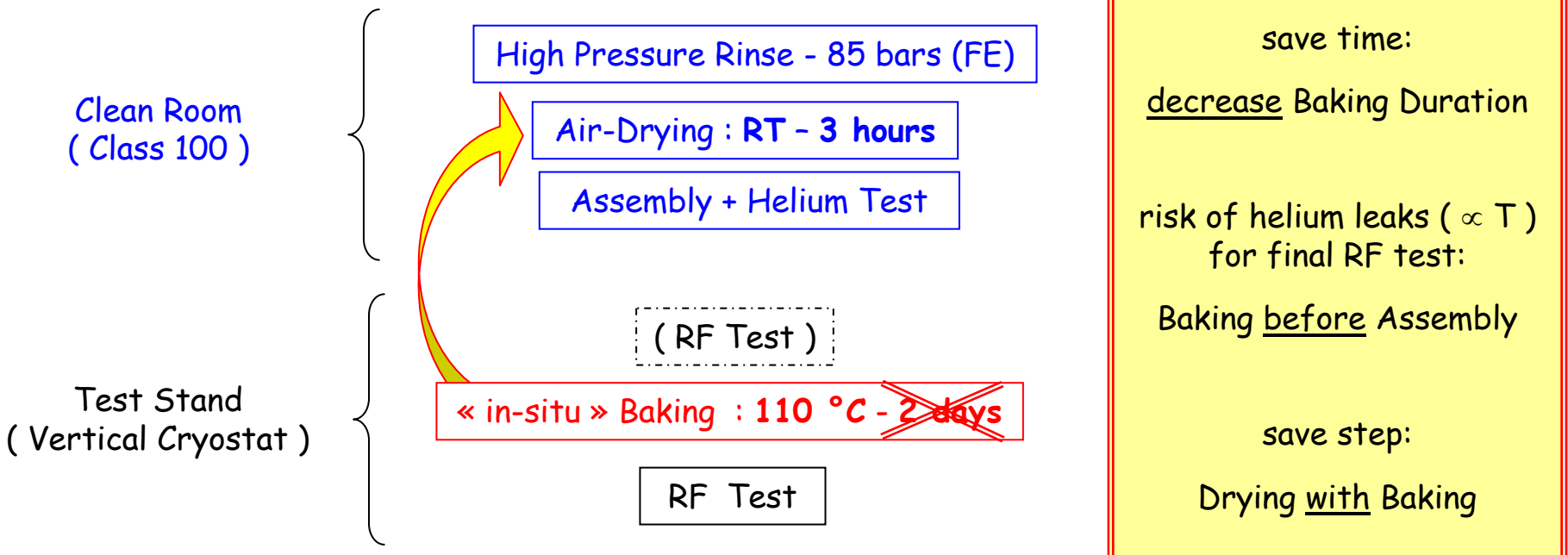


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# « In-Situ » Baking

*unadapted to*

# Cavity Mass Production





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# Hot Air - Drying

well adapted to

# Cavity Mass Production

Clean Room  
( Class 100 )



High Pressure Rinse - 85 bars (FE)

Hot Air-Drying : T - 3 hours

Assembly + Helium Test



Test Stand  
( Vertical Cryostat )

RF Test

save time:

decrease Baking Duration

risk of helium leaks ( $\propto T$ )  
for final RF test:

Baking before Assembly

save step:

Drying with Baking

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# High Field Q-Slope Improvement ?

avoid leaks

save time

combine with drying

« In-Situ » Baking	Modified Baking
Ultra High Vacuum	<b>Air</b> ( before assembly )
48 - 60 h ( 110 °C )	<b>3 hours</b> ( T ? )
Dry cavity	<b>Wet</b> cavity ( under laminar flow )

Some of these verifications  
have been already done,

R & D goes on for the others...



**Air-Drying**  
( RT → T ? )

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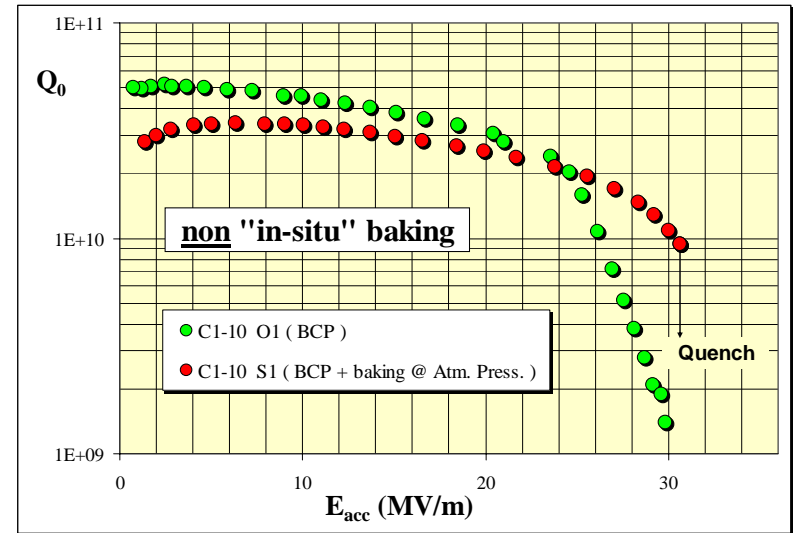
# « UHV » → « Air » Baking

Cavity open-ended in Stove

( room atmosphere - atmospheric pressure )



110 °C  
60 hours  
+ HPR



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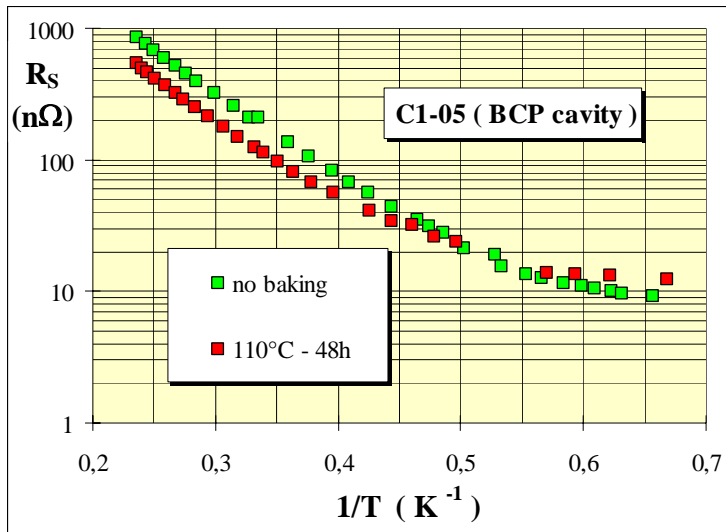
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# How to Decrease the Baking Duration ?

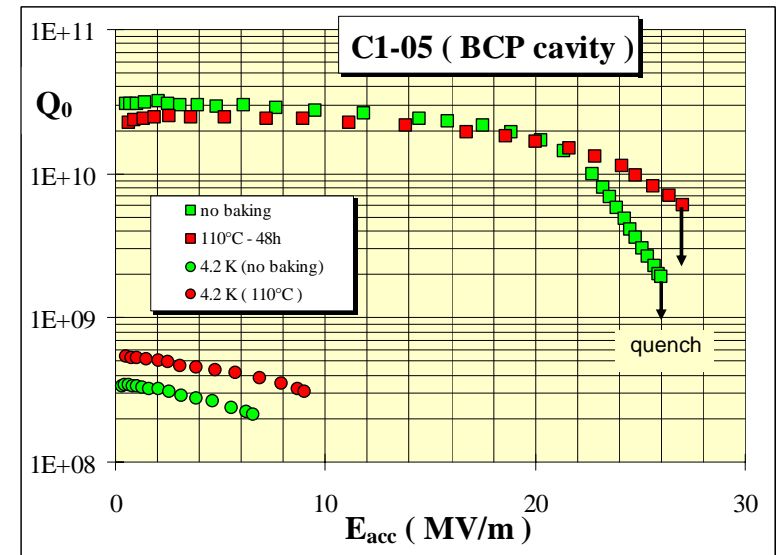
O diffusion modifies surface resistance  $R_S$  trough  $R_{BCS}(\ell)$

$$R_S = R_{res} + A(\lambda_L, \xi_F, \ell) \frac{\omega^2}{T} e^{-\Delta/kT}$$

High Field Q-slope improvement : mechanism is still unknown  
**Hypothesis** : O diffusion is involved



110 °C  
 60 hours  
 ( UHV )





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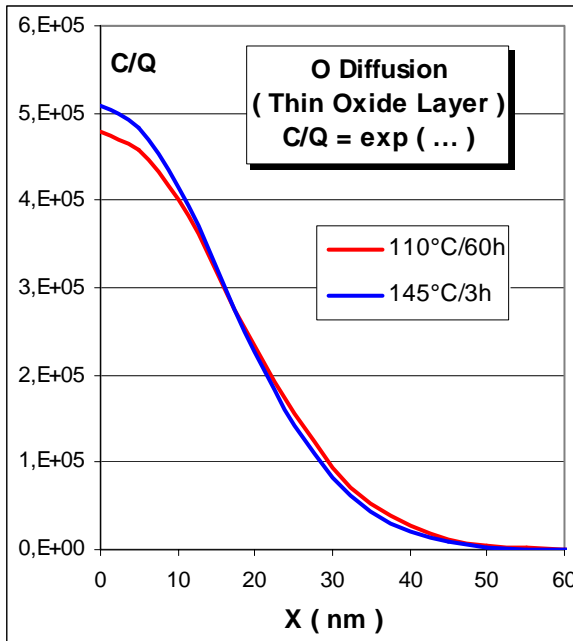


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# Oxygen Diffusion Parameters ( T , t )

$$\frac{\partial c}{\partial t} = D_0 e^{E_A/RT} \frac{\partial^2 c}{\partial x^2}$$

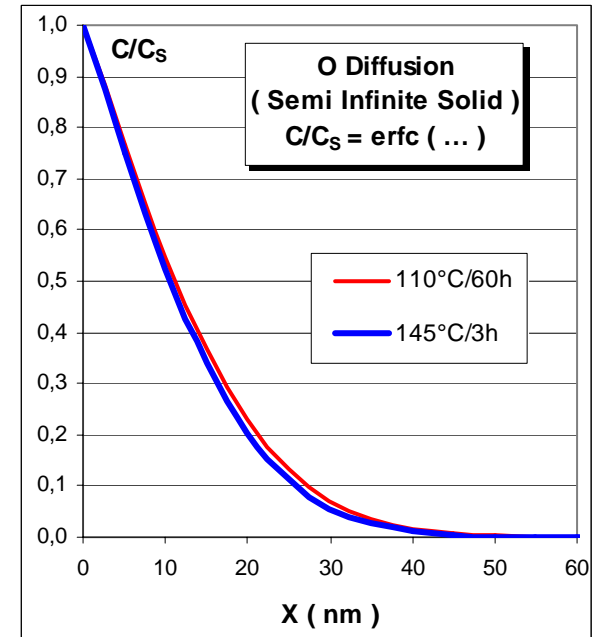
2<sup>nd</sup> Fick's law → analytic



110 °C / 60 hours



145 °C / 3 hours



thin oxide layer :  $C(x,0) = Q \delta(x)$

semi infinite solid :  $C(0,t) = C_s$

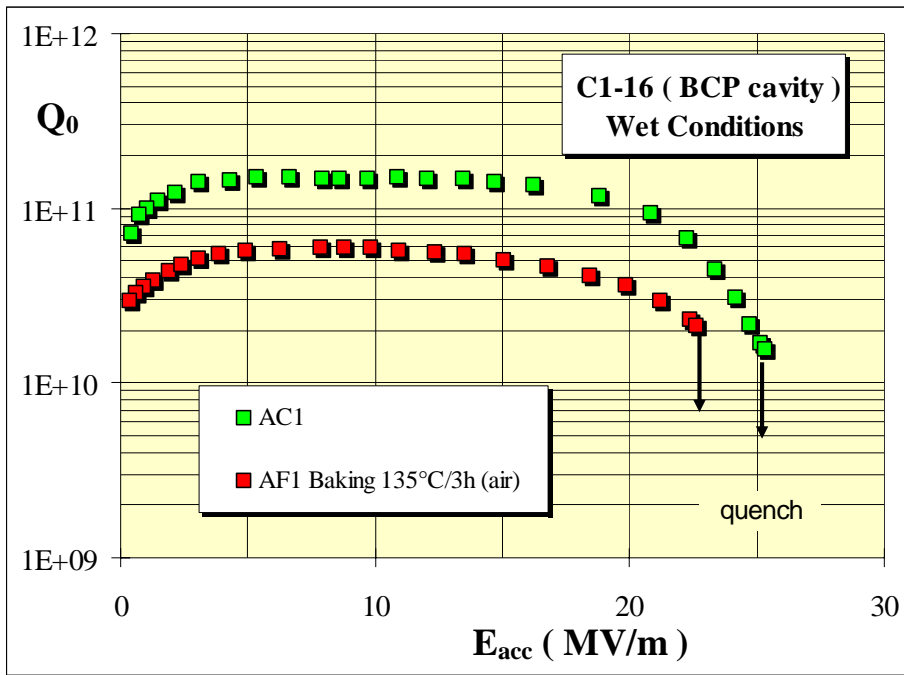
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# Fast Air-Baking on Wet Cavity

Very Bad Results



wrong hypothesis : diffusion ( T, t ) ?  
 surface degradation in stove ?  
 H<sub>2</sub>O on surface ?

160 °C  
 145 °C  
 135 °C

3 hours  
 + HPR



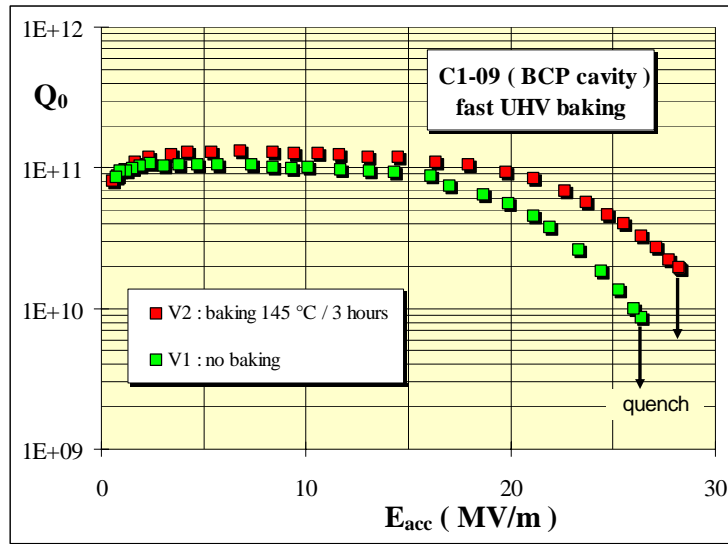
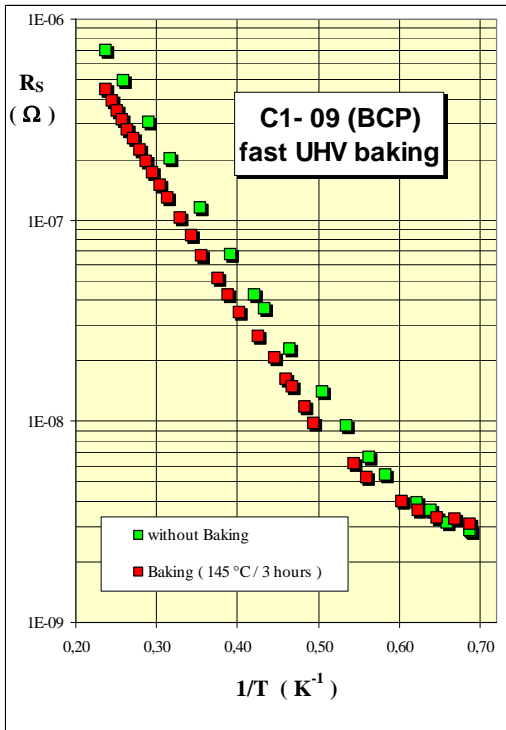
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# « Fast » Baking ( UHV )

- Cavity pumped out ( Ultra High Vacuum )
- Infra-Red emitters ( T : short rise time )



145 °C - 3 hours  
Right Hypothesis  
Q-slope ↔ O diffusion



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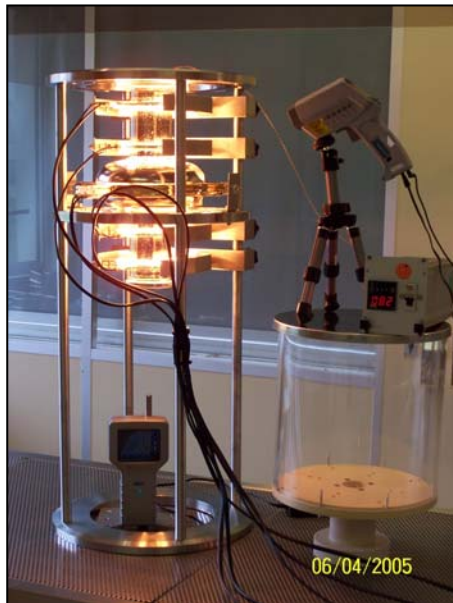
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# « *Fast* » *Baking ( Air )*

- Cavity open-ended

( Clean Room Atmosphere - Laminar Flow )

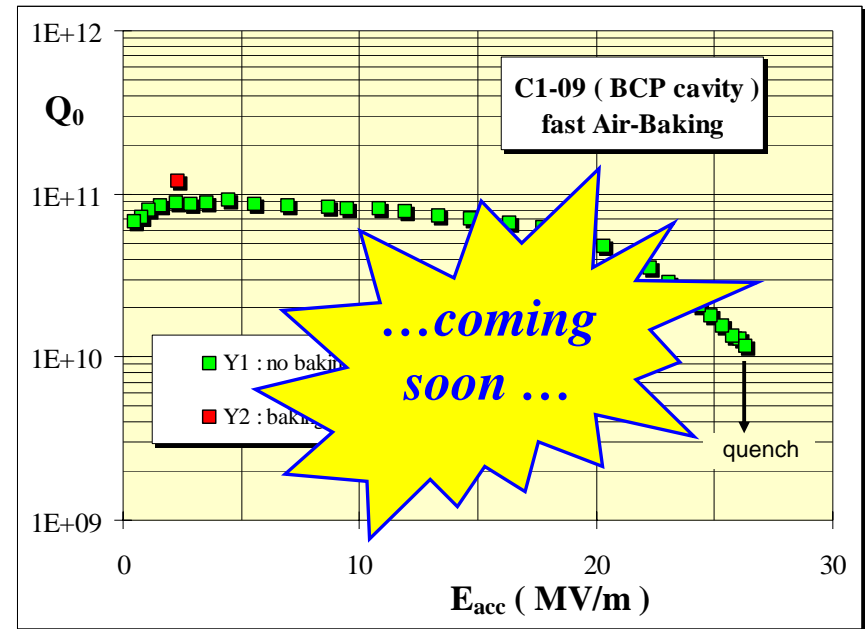
- Infra-Red emitters



145 °C  
3 hours  
+ HPR

Air contribution ?

( @ T > 110°C )



# Advances towards « Hot Air-Drying »

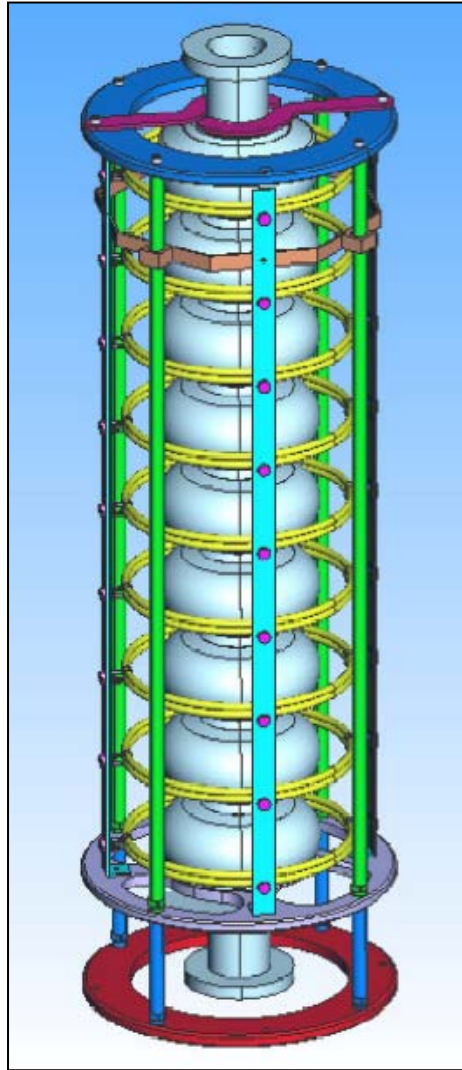
Baking + Air-Drying @ RT

« In-Situ » Baking		Fast Air-Baking
Ultra High Vacuum		Air 
48 - 60 h ( 110°C )		3 hours ( 145°C )
Dry cavity		Wet cavity

Solve Disturbances of Laminar Flow → Air-Drying @ 145 °C

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*from 1-cell  
to 9-cell Cavities  
....?....*

**Not a Problem !**

**System with I R emitters**

**could be easily adapted**

.....